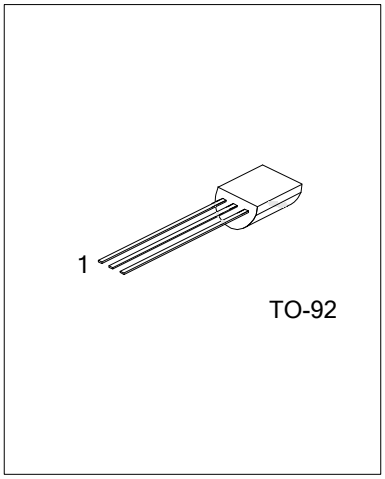
2SC3355

NPN SILICON EPITAXIAL TRANSISTOR

HIGH FREQUENCY LOW NOISE AMPLIFIER



■ FEATURES

* Low Noise and High Gain
* High Power Gain

■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC3355L-T92-B	2SC3355G-T92-B	TO-92	B	E	C	Tape Box
2SC3355L-T92-K	2SC3355G-T92-K	TO-92	B	E	C	Bulk

Note: Pin Assignment: B: Base E: Emitter C: Collector

2SC3355L-T92-B (1)Packing Type (2)Package Type (3)Lead Free	(1) B: Tape Box, K: Bulk (2) T92: TO-92 (3) L: Lead Free, G: Halogen Free

■ MARKING INFORMATION

PACKAGE	MARKING
TO-92	L: Lead Free G: Halogen Free UTC 2SC3355 □ □□□ Data Code 1

■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	12	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	100	mA
Total power dissipation	P_T	600	mW
Junction Temperature	T_J	125	°C
Operating Temperature	T_{OPR}	-20 ~ +85	°C
Storage Temperature	T_{STG}	-40 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	I_{CBO}	V_{CB}=10V, I_E=0			1.0	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=1V, I_C=0			1.0	μA
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=20mA	50		300	
Gain bandwidth Product	f_T	V_{CE}=10V, I_C=20mA		7		GHz
Feed-Back Capacitance	C_{re}	V_{CB}=10V, I_E=0, f=1.0MHz			1.0	pF
Noise Figure	NF	V_{CE}=10V, I_C=7mA, f=1.0GHz		1.1		dB